

**CMLT2907A**  
**SURFACE MOUNT**  
**DUAL PNP**  
**SILICON TRANSISTORS**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLT2907A consists of two individual, isolated 2907A PNP silicon transistors, manufactured by the epitaxial planar process and epoxy molded in an SOT-563 surface mount package. This PICOmini™ device has been designed for small signal general purpose and switching applications.

**MARKING CODE: L07**



**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

**SYMBOL**

$V_{CBO}$	60
$V_{CEO}$	60
$V_{EBO}$	5.0
$I_C$	600
$P_D$	350
$T_J, T_{stg}$	-65 to +150
$\theta_{JA}$	357

**UNITS**

V
V
V
mA
mW
$^\circ\text{C}$
$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=50\text{V}$		10	nA
$I_{CBO}$	$V_{CB}=50\text{V}, T_A=125^\circ\text{C}$		10	$\mu\text{A}$
$I_{CEV}$	$V_{CE}=30\text{V}, V_{BE}=0.5\text{V}$		50	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	60		V
$BV_{CEO}$	$I_C=10\text{mA}$	60		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.4	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.6	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		1.3	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.6	V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	75		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	100		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	100		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	50		

R2 (20-January 2010)

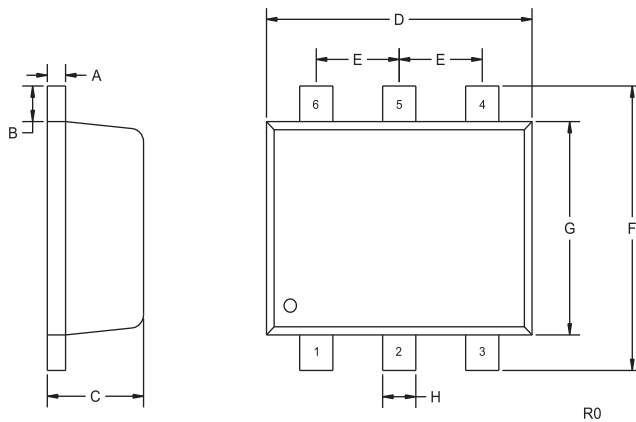
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**ELECTRICAL CHARACTERISTICS - Continued:**

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$f_T$	$V_{CE}=20V, I_C=50mA, f=100MHz$	200		MHz
$C_{ob}$	$V_{CB}=10V, I_E=0, f=1.0MHz$		8.0	pF
$C_{ib}$	$V_{BE}=2.0V, I_C=0, f=1.0MHz$		30	pF
$t_{on}$	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		45	ns
$t_d$	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		10	ns
$t_r$	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		40	ns
$t_{off}$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		100	ns
$t_s$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		80	ns
$t_f$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		30	ns

**SOT-563 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

**LEAD CODE:**

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

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